

isc Silicon NPN Power Transistor

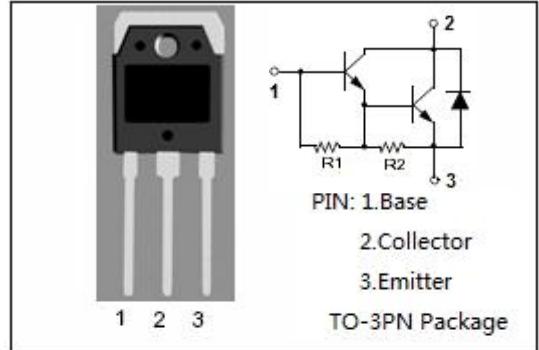
BU941P

DESCRIPTION

- High Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- High ruggedness electronic ignitions
- High voltage ignition coil driver

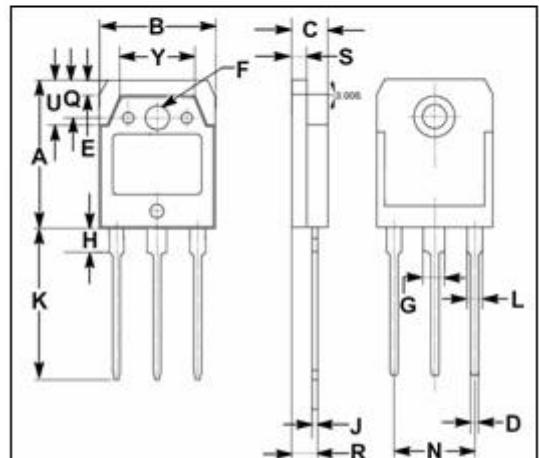


ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	5	V
I_c	Collector Current- Continuous	15	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current	1	A
I_{BM}	Base Current-Peak	5	A
P_c	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	155	W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	0.97	°C/W



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

isc Silicon NPN Power Transistor**BU941P****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage	I _C =50mA; I _B = 0	400			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 8 A; I _B = 100mA			1.6	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 10 A; I _B = 250mA			1.8	V
V _{CE(sat)-3}	Collector-Emitter Saturation Voltage	I _C = 12 A; I _B = 300mA			2.0	V
V _{BE(sat)-1}	Base-Emitter Saturation Voltage	I _C = 8 A; I _B = 100mA			2.2	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	I _C = 10 A; I _B = 250mA			2.5	V
V _{BE(sat)-3}	Base-Emitter Saturation Voltage	I _C = 12 A; I _B = 300mA			2.7	V
I _{CES}	Collector Cutoff Current	V _{CE} = 500V; V _{BE} = 0 V _{CE} = 500V; V _{BE} = 0; T _j = 125°C			0.1 0.5	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 450V; I _B = 0 V _{CE} = 450V; I _B = 0; T _j = 125°C			0.1 0.5	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			20	mA
h _{FE}	DC Current Gain	I _C = 5A ; V _{CE} = 10V	300			
V _{ECF}	C-E Diode Forward Voltage	I _F = 10A			2.5	V

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